

Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

Kropman, Daniel; Dolgov, Sergei; Onufrijevs, Pavels; Dauksta, Edvins Gettering and Defect Engineering in Semiconductor Technology XV 2014 / p. 352-357 : ill <https://doi.org/10.4028/www.scientific.net/SSP.205-206.352> [Conference proceedings at Scopus](#) [Article at Scopus](#) [Conference proceedings at WOS](#) [Article at WOS](#)

Low-K factor of SiO₂ layer on Si irradiated by YAG:Nd laser

Medvid, A.; Onufrijevs, Pavels; **Mellikov, Enn;** **Kropman, Daniel;** Muktepavela, F.; Bakradze, G. Journal of non-crystalline solids 2007 / p. 703-707 : ill <https://www.sciencedirect.com/science/article/pii/S0022309306014116>

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; **Mellikov, Enn;** Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf

Understanding and control of stress at Si-SiO₂ interface

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